

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L24	66705	(source and drain) with (depression recess\$2 groove\$1 trench\$2 hole vias cavit\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:50
L25	37945	L24 and ((insulat\$3 dielectric nonconduct\$3 non-conduct\$3) with (depression recess\$2 groove\$1 trench\$2 hole vias cavit\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:36
L26	30020	L25 and (gate near (oxide dielectric insulat\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:51
L27	4010	(257/372,373,374,386,396,397,E29.02,E29.021,E29.039,E29.12,E29.121,E29.122).CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/09/20 14:34
L28	53	((source and drain) with (depression recess\$2 groove\$1 trench\$2 hole vias cavit\$3)) same (seed near (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:50
L29	48	L28 and ((insulat\$3 dielectric nonconduct\$3 non-conduct\$3) with (depression recess\$2 groove\$1 trench\$2 hole vias cavit\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:36
L30	36	L29 and (gate near (oxide dielectric insulat\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:53

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L31	1	L30 and L27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:36
L32	2919	((source and drain) and (depression recess\$2 groove\$1 trench\$2 hole vias cavit\$3)) and (seed near (layer film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:50
L33	1431	L32 and (gate near (oxide dielectric insulat\$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:52
L34	21	L33 and L27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:53
L35	32	(L29 L34) not (L31 L30)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:55
L36	5	L28 not (L29 L34 L31 L30)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:57
L37	1371	L33 not (L28 L29 L34 L31 L30)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:57

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L38	1290	L37 and ("257"/\$.ccls. "438"/\$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 14:57
L39	1287	L37 and (transistor FET (field near effect near transistor))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/20 15:05

Interference Search

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L41	10	(source and drain and seed and (gate near (oxide insulat\$3 dielectric)) and (depression recess\$2 trench\$2 cavit\$3 vias hole groove\$1) and ((field near effect near transistor) FET MOSFET)).clm.	US-PGPUB	OR	ON	2007/09/20 16:56
L42	49	(source and drain and seed and (gate near (oxide insulat\$3 dielectric)) and (depression recess\$2 trench\$2 cavit\$3 vias hole groove\$1)).clm.	US-PGPUB	OR	ON	2007/09/20 16:56